



ACE11205A

P-Channel Enhancement Mode MOSFET

Description

The ACE11205A is the P-Channel enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high-density process is especially tailored to minimize on-state resistance and provide superior switching performance.

These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where high-side switching, low in-line power loss, and resistance to transients are needed.

Features

- -20V/0.45A, $R_{DS(ON)} = 520m\Omega @ V_{GS} = -4.5V$
- -20V/0.35A, $R_{DS(ON)} = 700m\Omega @ V_{GS} = -2.5V$
- -20V/0.25A, $R_{DS(ON)} = 1500m\Omega @ V_{GS} = -1.8V$
- Super high-density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

Application

- Drivers: Relays/Solenoids/Lamps/Hammers
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

Absolute Maximum Ratings

| Parameter | Symbol | Max | Unit |
|--|-----------------|--------------------|------------|
| Drain-Source Voltage | V_{DSS} | -20 | V |
| Gate-Source Voltage | V_{GSS} | ± 12 | V |
| Continuous Drain Current ($T_J = 150^\circ C$) | I_D | $T_A = 25^\circ C$ | -1.0 |
| | | $T_A = 80^\circ C$ | -0.7 |
| Pulsed Drain Current | I_{DM} | -3 | A |
| Continuous Source Current (Diode Conduction) | I_S | -0.6 | A |
| Power Dissipation | P_D | $T_A = 25^\circ C$ | 0.35 |
| | | $T_A = 70^\circ C$ | 0.19 |
| Operating Junction Temperature | T_J | -55/150 | $^\circ C$ |
| Storage Temperature Range | T_{STG} | -55/150 | $^\circ C$ |
| Thermal Resistance-Junction to Ambient | $R_{\theta JA}$ | $T \leq 10sec$ | 360 |
| | | Steady State | 400 |

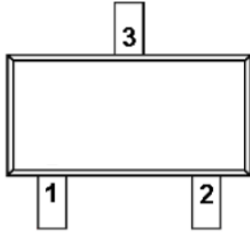


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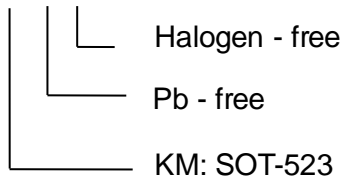
Packaging Type

SOT-523



Ordering information

ACE11205A XX + H





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Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Technology Co., LTD. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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